



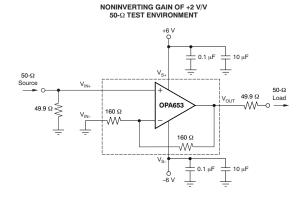
Wideband, Fixed Gain, JFET-Input AMPLIFIER

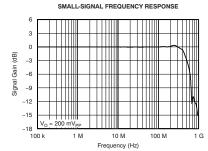
FEATURES

- HIGH BANDWIDTH: 500 MHz (G = +2 V/V)
- HIGH SLEW RATE: 2675 V/µs (4-V Step)
- EXCELLENT THD: -71dBc at 10 MHz
- LOW INPUT VOLTAGE NOISE: 6.1 nV/√Hz
- FAST OVERDRIVE RECOVERY: 8 ns
- FAST SETTLING TIME (1% 4-V Step): 7.9 ns
- LOW INPUT OFFSET VOLTAGE: ±1 mV
- LOW INPUT BIAS CURRENT: ±10 pA
- HIGH INPUT IMPEDANCE: 10¹² Ω||2.5 pF
- INTERNAL GAIN SETTING RESISTORS:
 G = +2 V/V or G = -1 V/V
- HIGH OUTPUT CURRENT: 70 mA

APPLICATIONS

- TEST AND MEASUREMENT FRONT-END
- HIGH-INPUT IMPEDANCE PROBES
- DATA ACQUISITION CARDS
- OSCILLOSCOPE INPUT
- ADC INPUT AMPLIFIER





DESCRIPTION

The OPA653 combines a very wideband voltage-feedback operational amplifier with a JFET-input stage with internal gain setting resistors to achieve an ultra-high, dynamic-range amplifier for fixed gain of +2-V/V or -1-V/V applications.

The 500-MHz wide gain of +2-V/V bandwidth is complemented by a very high 2675-V/µs slew rate and fast settling time that make it ideal for time-domain and pulse-oriented applications.

Excellent -72-dBc THD distortion performance at 10 MHz makes the OPA653 an excellent choice for frequency-domain and FFT analysis applications.

Additionally, with the low 6.1-nV/\(\sqrt{Hz}\) voltage noise, low bias current, and high impedance JFET input, it supports very low noise, wideband, high input impedance applications. Examples include high-impedance probes, data acquisition cards, and oscilloscope front-ends.

RELATED OPERATIONAL AMPLIFIER PRODUCTS

DEVICE	V _s (V)	BW (MHz)	SLEW RATE (V/μs)	VOLTAGE NOISE (nV/√Hz)	AMPLIFIER DESCRIPTION
OPA356	+5	200	300	5.80	Unity-Gain Stable CMOS
OPA656	±5	500	290	7	Unity-Gain Stable JFET-Input
OPA657	±5	350	700	4.8	Gain of +7 Stable JFET-Input
OPA659	±6	650	2550	8.9	Unity-Gain Stable JFET-Input
THS4631	±15	105	900	7	Unity-Gain Stable JFET-Input

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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ORDERING INFORMATION(1)

PRODUCT	PACKAGE-LEAD	PACKAGE DESIGNATOR	SPECIFIED TEMPERATURE RANGE	PACKAGE MARKING	ORDERING NUMBER	TRANSPORT MEDIA, QUANTITY	
OPA653	SOT23-5	DBV	-40°C to +85°C	BZW	OPA653IDBVT	Tape and Reel, 250	
OFA655	30123-3	DBV	- 4 0 0 to +00 0	40 0 10 100 0	DZVV	OPA653IDBVR	Tape and Reel, 3000
OPA653	VSON-8	DRB	-40°C to +85°C	OBEI	OPA653IDRBT	Tape and Reel, 250	
OPA655	V3ON-6	DKB	-40 C to +65 C	OBEI	OPA653IDRBR	Tape and Reel, 3000	

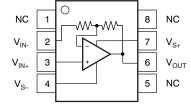
⁽¹⁾ For the most current package and ordering information see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

ABSOLUTE MAXIMUM RATINGS

Over operating free-air temperature range (unless otherwise noted).

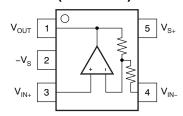
		OPA653	UNIT
Power Su	pply Voltage V _{S+} to V _{S-}	±6.5	V
Input Volta	age	±V _S	V
Input Curr	ent	100	mA
Output Cu	rrent	100	mA
Continuou	s Power Dissipation	See Thermal	Characteristics
Operating	Operating Free Air Temperature Range, T _A -40 to +85		°C
Storage Temperature Range		-65 to +150	°C
Lead Tem	perature (soldering, 10s)	+260	°C
Maximum Junction Temperature, T _J		+150	°C
Maximum	Junction Temperature, T _J (continuous operation for long term reliability)	+125	°C
	Human Body Model (HBM)	4000	V
ESD Rating:	Charge Device Model (CDM)	1000	V
raung.	Machine Model	200	V

DRB PACKAGE VSON-8 (TOP VIEW)



Note: NC: No connection.

DRV PACKAGE SOT23-5 (TOP VIEW)





ELECTRICAL CHARACTERISTICS: V_s = ±6 V

At G = +2 V/V, R_L = 100 Ω , and T_A = +25°C, unless otherwise noted.

			OPA653			TEST
PARAMETER	CONDITIONS	MIN	MIN TYP MAX			LEVEL ⁽¹⁾
AC PERFORMANCE						
Small-Signal Bandwidth	$V_O = 200 \text{ mV}_{PP}$		500		MHz	С
Bandwidth for 0.1-dB Flatness	$V_{O} = 2 V_{PP}$		75		MHz	С
Large-Signal Bandwidth	$V_{O} = 2 V_{PP}$		475		MHz	В
Slew Rate	V _O = 4-V Step		2675		V/µs	В
Rise and Fall Time	V _O = 4-V Step		1.3		ns	С
Settling Time to 1%	V _O = 4-V Step		7.9		ns	С
Pulse Response Overshoot	V _O = 4-V Step		14		%	С
Harmonic Distortion	$f = 10 \text{ MHz}, V_O = 2 V_{PP}$					
2nd harmonic			-72		dBc	С
3rd harmonic			-90		dBc	С
Intermodulation Distortion	$V_O = 2-V_{PP}$ envelope (each tone 1 V_{PP}), $f_1 = 10$ MHz, $f_2 = 11$ MHz					
Second-order Intermodulation			-75		dBc	С
Third-order Intermodulation			-96		dBc	С
Input Voltage Noise	f > 100 kHz		6.1		nV/√ Hz	С
Input Current Noise	f > 100 kHz		1.8		fA/√Hz	С
DC PERFORMANCE						
Gain Error	T _A = +25°C		±0.5	±1.25	%	Α
	$T_A = -40^{\circ} \text{ C to } +85^{\circ} \text{C}$		±0.6	±1.35	%	В
Internal R _F and R _G		140	160	180	Ω	Α
Open-Loop Voltage Gain (A _{OL}) ⁽²⁾			62		dB	С
Input Offset Voltage	$T_A = +25^{\circ}C, V_{CM} = 0 V$		±1	±5	mV	Α
	$T_A = -40$ °C to +85°C, $V_{CM} = 0 \text{ V}$		±3	±7	mV	В
Average input offset voltage drift	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C, \ V_{CM} = 0 \text{ V}$		±15	±30	μV/°C	В
Input Bias Current, Noninverting input	$T_A = +25^{\circ}C, V_{CM} = 0 V$		±10	±50	pA	Α
	$T_A = 0$ °C to + 70°C, $V_{CM} = 0$ V		±240	±1200	pA	В
	$T_A = -40$ °C to +85°C, $V_{CM} = 0 \text{ V}$		±640	±3200	pA	В
Average input bias current drift, noninverting input	$T_A = 0^{\circ}C \text{ to } +70^{\circ}C, \ V_{CM} = 0 \ V$		±5	±26	pA/°C	В
	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C, \ V_{CM} = 0 \text{ V}$		±7	±34	pA/°C	В
INPUT						
Input Voltage Range	$V_{IN+} = V_{IN-}$		±3.5		V	С
Noninverting Input Impedance			10 ¹² 2.5		Ω ∥ pF	С
OUTPUT						
Output Voltage Swing	$T_A = +25$ °C, No load	±4.35	±4.45		V	Α
	$T_A = +25$ °C, $R_L = 100 \Omega$	±3.2	±3.6		V	Α
Output Voltage Swing	$T_A = -40$ °C to +85°C, No load	±4.2	±4.3		V	В
	$T_A = -40$ °C to +85°C, $R_L = 100 \Omega$	±3.07	±3.2		V	В
Output Current, Sourcing, Sinking	T _A = +25°C	±60	±70		mA	Α
	$T_A = -40$ °C to +85°C	±56	±66		mA	В
Closed-Loop Output Impedance	f = 100 kHz		0.16		Ω	С

Test levels: (A) 100% tested at +25°C. Over temperature limits set by characterization and simulation. (B) Limits set by characterization and simulation. **(C)** Typical value only for information.

Open loop gain is for informational use only. Open loop gain is from simulation and not measured in a closed-loop amplifier.



ELECTRICAL CHARACTERISTICS: V_S = ±6 V (continued)

At G = +2 V/V, R_L = 100 Ω , and T_A = +25°C, unless otherwise noted.

PARAMETER				OPA653		TEST LEVEL ⁽¹⁾	
		CONDITIONS	MIN	MIN TYP			UNIT
POWER SUPPLY							
Specified Operating Voltage	е	$T_A = -40$ °C to +85°C	±3.5	±6	±6.5	V	В
Quiescent Current		$T_A = +25^{\circ}C$	30.5	32	33.5	mA	Α
		$T_A = -40$ °C to +85°C	28.3		35.7	mA	В
Power-Supply Rejection Ratio		$T_A = +25^{\circ}C$, $\pm V_S = 5.5 \text{ V to } 6.5 \text{ V}$	62	66	dB	Α	
		$T_A = -40$ °C to +85°C, ± $V_S = 5.5$ V to 6.5 V	60	64		dB	В
THERMAL CHARACTERIS	STICS						
Specified Operating Range DBV and DRB Packages			-40		+85	°C	С
Thermal Resistance, θ_{JA}		Junction-to-ambient					
DBV	SOT23-5			105		°C/W	С
DRB	VSON-8			55		°C/W	С

TYPICAL CHARACTERISTICS

Table of Graphs

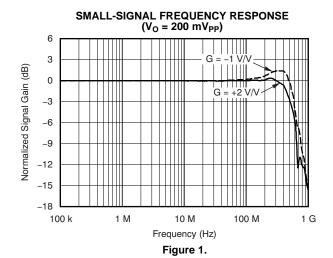
TITLE		FIGURE
Small-Signal Frequency Response	$V_O = 200 \text{ mV}_{PP}$	Figure 1
Noninverting Large-Signal Frequency Response	Gain = +2 V/V	Figure 2
Inverting Large-Signal Frequency Response	Gain = -1 V/V	Figure 3
Input-Referred Voltage and Current Noise Spectral Density		Figure 4
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Recommended R _{ISO} vs Capacitive Load	Figure 17	
Closed-Loop Output Impedance vs Frequency	Figure 18	
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TYPICAL CHARACTERISTICS: V_S = ±6 V

At G = +2 V/V, R_L = 100 Ω , and T_A = +25°C, unless otherwise noted.



NONINVERTING LARGE-SIGNAL FREQUENCY RESPONSE

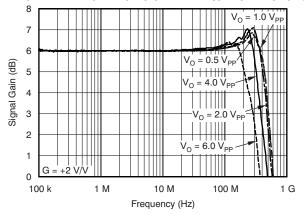
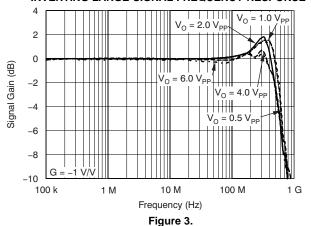
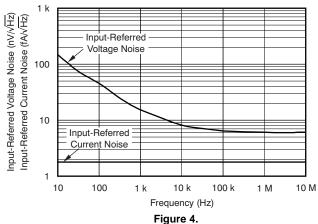


Figure 2.

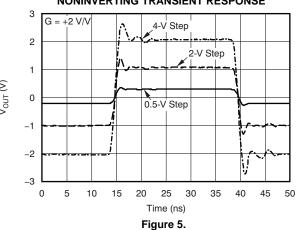
INVERTING LARGE-SIGNAL FREQUENCY RESPONSE



INPUT-REFERRED VOLTAGE AND CURRENT NOISE SPECTRAL DENSITY



NONINVERTING TRANSIENT RESPONSE



INVERTING TRANSIENT RESPONSE

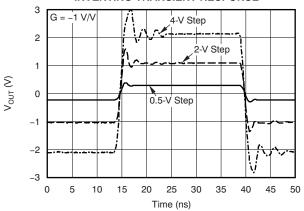


Figure 6.

INSTRUMENTS

TYPICAL CHARACTERISTICS: V_s = ±6 V (continued)

At G = +2 V/V, R_L = 100 Ω , and T_A = +25°C, unless otherwise noted.

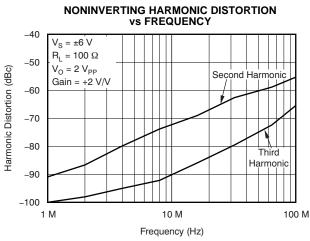


Figure 7.

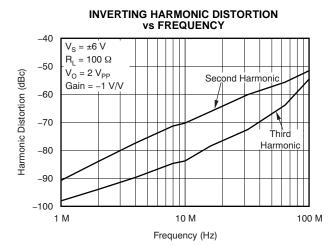


Figure 8.

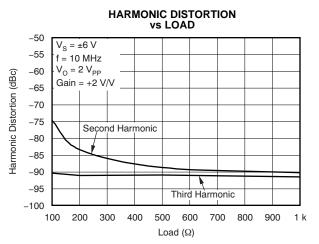
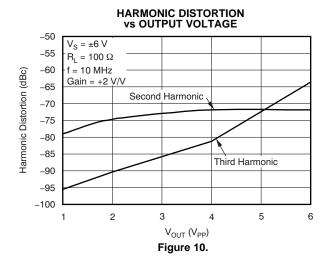
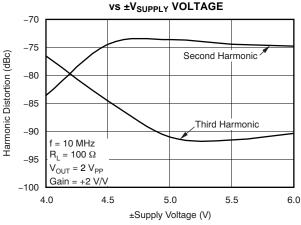
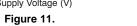


Figure 9. HARMONIC DISTORTION



TWO-TONE INTERMODULATION DISTORTION vs FREQUENCY





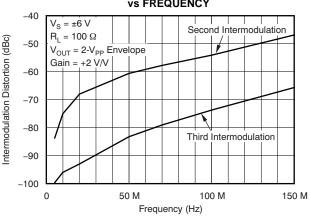


Figure 12.

TYPICAL CHARACTERISTICS: V_S = ±6 V (continued)

At G = +2 V/V, R_L = 100 Ω , and T_A = +25°C, unless otherwise noted.

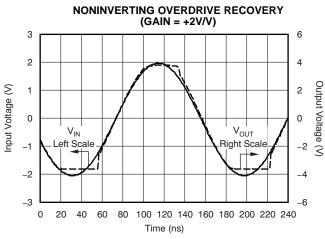


Figure 13.

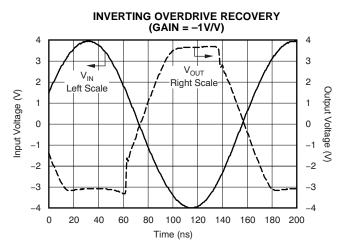


Figure 14.

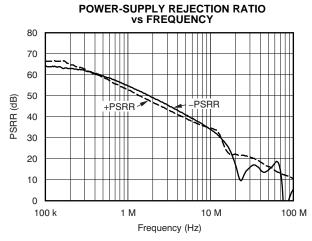


Figure 15.

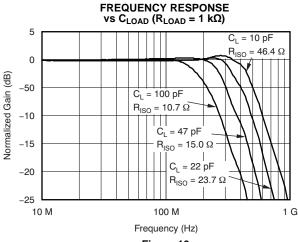
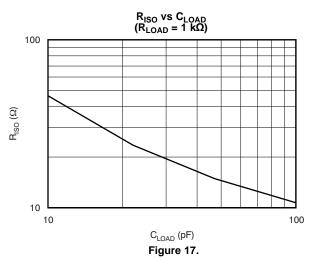


Figure 16.



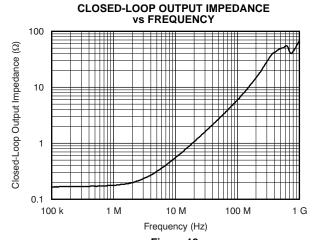
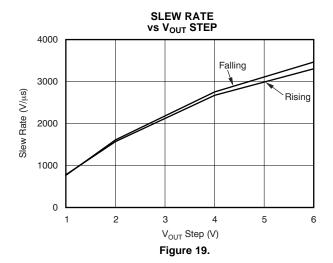


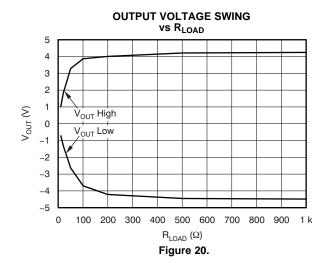
Figure 18.



TYPICAL CHARACTERISTICS: $V_s = \pm 6 \text{ V (continued)}$

At G = +2 V/V, R_L = 100 Ω , and T_A = +25°C, unless otherwise noted.





APPLICATION INFORMATION

Wideband, Noninverting, and Inverting Operation

The OPA653 is a very broadband, voltage-feedback amplifier with internal gain-setting resistors that set a fixed gain of +2 V/V or -1 V/V and a high-impedance JFET-input stage. Its very high bandwidth of 500 MHz can be used to either deliver high signal bandwidths at a gain of +2 V/V or, if driven from a low-impedance source, a gain of -1 V/V . The OPA653 is designed to provide very low noise and accurate pulse response with low overshoot and ringing. To achieve the full performance of the OPA653, careful attention to printed circuit board (PCB) layout and component selection is required as discussed in the remaining sections of this data sheet.

Figure 21 shows the noninverting gain of +2-V/V circuit that is used as the basis for the Typical Characteristics. Most of the curves characterized using signal sources with 50-Ω driving impedance, and with measurement equipment that presents a $50-\Omega$ load impedance. In Figure 21, the $^{\cdot}$ 49.9-Ω shunt resistor to ground at the $V_{\text{IN+}}$ input is used to match the source impedance of the test generator and cable, while the $49.9-\Omega$ series output resistor V_{OUT} provides matching impedance for the measurement equipment load and cable. Data sheet voltage swing specifications are taken at the noninverting input pin, V_{IN+} , or the output pin, V_{OUT} , unless otherwise noted.

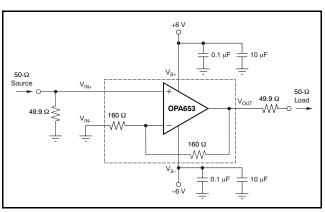


Figure 21. Noninverting Gain of +2 V/V in 50-Ω
Test Environment

Figure 22 shows the OPA653 in a noninverting gain of -1 V/V configuration in a 50- Ω test environment as was used for testing the Typical Characteristics. The circuit operation is essentially the same as Figure 21 except that a 72.3- Ω termination resistor is now used between the V_{IN} input and ground, so that together with the gain-setting resistor (R_G = 160 Ω), the input impedance is approximately 50 Ω . The V_{IN+} input is terminated to ground using a 49.9- Ω resistor as a precaution to avoid single transistor oscillations at the input; the value is not critical, but attention should be paid to avoid large values because of the noise contribution as noted below.

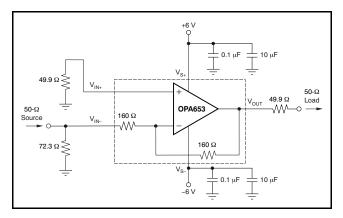


Figure 22. Noninverting Gain of –1 V/V in 50-Ω Test Environment

Note that the 72.3- Ω input termination resistor and the 50- Ω source impedance of the test equipment modify the noise gain to +1.84 V/V and the amplifier is compensated for optimal performance with a noise gain of +2 V/V. This compensation reduces the phase margin and results in more peaking in the frequency response and more overshoot/ringing in the pulse response. This effect can be seen by comparing the inverting and noninverting frequency and pulse response graphs in the characteristic data. The amplifier phase margin can be restored in an application that uses an inverting configuration if it is driven from a very low impedance source such as an op amp.



OPERATING SUGGESTIONS

Setting Resistor Values to Minimize Noise

The OPA653 provides a low input noise voltage. Figure 23 shows the op amp noise analysis model with all the noise terms included. In this model, all the noise terms are taken to be noise voltage or current density terms in either nV/\sqrt{Hz} or pA/\sqrt{Hz} .

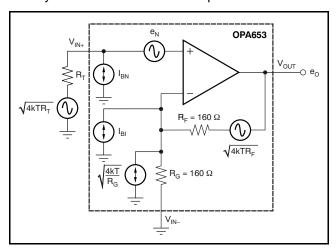


Figure 23. Noise Analysis Circuit

The total output spot noise voltage can be computed as the square root of the squared contributing terms to the output noise voltage. This calculation adds all the contributing noise powers at the output by superposition, then takes the square root to return to a spot noise voltage. Equation 1 shows the general form for this output noise voltage using the terms shown in Figure 23.

$$\Theta_{O} = \sqrt{\left[4kTR_{T} + (I_{BN}R_{T})^{2} + e_{N}^{2}\right]\left[1 + \frac{R_{F}}{R_{G}}\right]^{2} + (I_{BI}R_{F})^{2} + 4kTR_{F}\left[1 + \frac{R_{F}}{R_{G}}\right]}$$
(1)

Dividing this expression by the noise gain = 1 + R_F/R_G gives the equivalent input-referred spot noise voltage at the noninverting input as shown in Equation 2

$$e_{NI} = \sqrt{4kTR_{T} + (I_{BN}R_{T})^{2} + e_{N}^{2} + \left(\frac{I_{BI}R_{F}}{2}\right)^{2} + \left(\frac{4kTR_{F}}{2}\right)}$$
(2)

Putting high resistor values into Equation 2 can quickly dominate the total equivalent input-referred noise. Because the gain-setting resistors, R_F and R_G , are internal to the device, the user cannot change this noise contribution, and the noise gain is equal to +2 V/V.

However, attention should be paid to the value of R_T or other source impedance on the noninverting input. High-value resistive impedance on the noninverting input can add significant noise; for example, 2.4 k Ω adds a Johnson voltage noise term equal to the amplifier itself (6.2 nV/ $\sqrt{\text{Hz}}$). So while the JFET input of the OPA653 is ideal for high source impedance applications in the noninverting configuration of Figure 21, the overall bandwidth and noise are limited by high source impedances.

Driving Capacitive Loads

One of the most demanding and yet very common load conditions for an op amp is capacitive loading. The OPA653 is very robust, but care should be taken with light loading scenarios so output capacitance does not lead to decreased stability, increased frequency response peaking, overshoot, and ringing. When the amplifier output resistance is considered, capacitive loading introduces an additional pole in the signal path that reduces the phase margin. Several external solutions to this problem have been suggested for standard op amps. Because the OPA653 has internal gain-setting resistors, the only real option is to use a series output resistor. This option is a good solution because when the primary considerations are frequency response flatness, pulse response fidelity, and/or distortion, a series output resistor is the simplest and most effective technique. The idea is to isolate the capacitive load from the feedback loop by inserting a series isolation resistor, R_{ISO}, between the amplifier output and the capacitive load as shown in Figure 24 below. In effect, this configuration isolates the phase shift from the loop gain of the amplifier, thus restoring the phase margin and improving stability.

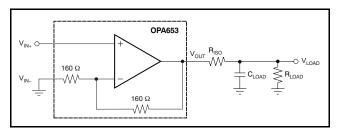


Figure 24. Adding Series Ouput Resistance to Isolate Capacitive Loads

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The Typical Characteristics show the recommended R_{ISO} versus Capacitive Load performance (see Figure 17) and the resulting frequency response with a 1- $k\Omega$ load. Note that larger R_{ISO} values are required for lower capacitive loading. In this case, a design target of a maximally-flat frequency response was used. Lower values of RISO may be used if some peaking can be tolerated. Long PCB traces, unmatched cables, and connections to multiple devices can easily degrade the performance of the OPA653. Always consider this effect carefully, and add the recommended series resistor as close as possible to the OPA653 output pin (see the Board Layout section). With heavier loads (for example, the 100- Ω load presented in the test circuits used for testing the Typical Characteristics), the OPA653 is very robust; R_{ISO} can be as low as 10 Ω with capacitive loads less than 5 pF and continue to show a flat frequency response.

Distortion Performance

The OPA653 is capable of delivering low distortion at high frequencies. The distortion plots in the Typical Characteristics show the typical distortion under a wide variety of conditions. Generally, the best distortion performance can be achieved using higher power-supply voltage (±6 V is recommended), lower output voltage swings, and lower loads.

The total load includes the feedback network—in the noninverting configuration, this value is the sum of $R_F + R_G = 320~\Omega$, while in the inverting configuration the total load is only $R_F = 160~\Omega$ (see Figure 22).

Power-supply decoupling is critical for harmonic distortion performance. In particular, for optimal second-harmonic performance, the high-frequency, 0.1- μ F, power-supply decoupling capacitors should be as close as posible to the positive and negative supply pins and should be brought to a single point ground away from the input pins.

Pulse and Transient Response

To achieve optimum pulse and transient response, the OPA653 should be used in a noise gain of +2 V/V configuration, with minimal capacitance at the output, and high-frequency, 0.1- μ F, power-supply decoupling capacitors as close the power pins as possible.

Note: Noise gain of +2 V/V is achieved by tying V_{IN-} to a 0- Ω point. In noninverting gain of +2 V/V applications, V_{IN-} should be grounded, and in inverting gain of -1 V/V applications, V_{IN-} should be driven from a near-0- Ω source such as an op amp.

Board Layout

Achieving optimum performance with a high-frequency amplifier such as the OPA653 requires careful attention to PCB layout parasitics and external component types. Recommendations that can optimize device performance include the following.

- a) Minimize parasitic capacitance to any ac ground for all of the signal input/output (I/O) pins. Parasitic capacitance on the output and inverting input pins can cause instability: on the noninverting input, it can react with the source impedance to cause unintentional band-limiting. To reduce unwanted capacitance, a window around the signal I/O pins should be opened in all of the ground and power planes around those pins. Otherwise, ground and power planes should be unbroken elsewhere on the board.
- b) Minimize the distance (less than 0.25 in, or 6,35 from the power-supply pins to high-frequency, 0.1-μF decoupling capacitors. At the device pins, the ground and power plane layout should not be in close proximity to the signal I/O pins. Use a single point ground, located away from the input pins, for the positive and negative supply high-frequency, 0.1-μF decoupling capacitors. Avoid narrow power and ground traces to minimize inductance between the pins and the decoupling capacitors. The power-supply connections should always be decoupled with these capacitors. Larger (2.2-μF to 10-μF) decoupling capacitors, effective at lower frequencies, should also be used on the supply pins. These larger capacitors may be placed somewhat farther from the device and may be shared among several devices in the same area of the PCB.
- c) Careful selection and placement of external components preserves the high-frequency performance of the OPA653. Resistors should be a very low reactance type. Surface-mount resistors work best and allow a tighter overall layout. Metal film and carbon composition, axially-leaded resistors can also provide good high-frequency performance. Again, keep the leads and PCB trace length as short as possible. Never use wirewound-type resistors in a high-frequency application. The inverting input pin is the most sensitive to parasitic capacitance; consequently, always position the feedback resistor as close to the negative input as possible. The output is also sensitive to parasitic capacitance; therefore, position a series output resistor (in this case, R_{ISO}) as close to the output pin as possible.

INSTRUMENTS

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Other network components, such as noninverting input termination resistors, should also be placed close to the package. Even with a low parasitic capacitance, excessively high resistor values can create significant time constants that can degrade device performance. Good axial metal film or surface-mount resistors have approximately 0.2 pF in shunt with the resistor. For resistor values greater than 1.5 k Ω , this parasitic capacitance can add a pole and/or zero below 500 MHz that can affect circuit operation. Keep resistor values as low as possible. Using values less than 500 Ω automatically holds the resistor noise terms low, and minimizes the effects of parasitic capacitance.

d) Connections to other wideband devices on the board may be made with short direct traces or through onboard transmission lines. For short connections, consider the trace and the input to the next device as a lumped capacitive load. Relatively wide traces (50 mils to 100 mils, or 1,27 cm to 2,54 cm) should be used. Estimate the total capacitive load and set $R_{\rm ISO}$ from the plot of *Recommended R_{ISO}* vs Capacitive Load (Figure 17). Low parasitic capacitive loads (less than 5 pF) may not need an $R_{\rm ISO}$ because the OPA653 is nominally compensated to operate with a 2-pF parasitic load.

Higher parasitic capacitive loads without an R_{ISO} are allowed as the signal gain increases (increasing the unloaded phase margin). If a long trace is required, 6-dB signal loss intrinsic doubly-terminated transmission line is acceptable, implement a matched impedance transmission line using microstrip or stripline techniques (consult an ECL design handbook for microstrip and stripline layout techniques). A $50-\Omega$ environment is normally not necessary onboard, and in fact a higher impedance environment improves distortion as shown in the distortion versus load plots. With a characteristic board trace impedance defined based on board material and trace dimensions, a matching series resistor into the trace from the output of the OPA653 is used as well as a terminating shunt resistor at the input of the destination device. Remember also that the terminating impedance is the parallel combination of the shunt resistor and the input impedance of the destination device: this total effective impedance should be set to match the trace impedance. lf the 6-dB attenuation doubly-terminated transmission line is unacceptable. a long trace can be series-terminated at the source end only. Treat the trace as a capacitive load in this

case, and set the series resistor value as shown in the plot of $R_{\rm ISO}$ vs Capacitive Load (Figure 17). This configuration does not preserve signal integrity as well as a doubly-terminated line. If the input impedance of the destination device is low, there will be some signal attenuation as a result of the voltage divider formed by the series output into the terminating impedance.

e) Socketing a high-speed part such as the OPA653 is not recommended. The additional lead length and pin-to-pin capacitance introduced by the socket can create an extremely troublesome parasitic network that can make it almost impossible to achieve a smooth, stable frequency response. Best results are obtained by soldering the OPA653 directly onto the board.

Input and ESD Protection

The OPA653 is built using a very high-speed complementary bipolar process. The internal junction breakdown voltages are relatively low for these very small geometry devices. These breakdowns are reflected in the Absolute Maximum Ratings table. All device pins are protected with internal ESD protection diodes to the power supplies, as Figure 25 shows.

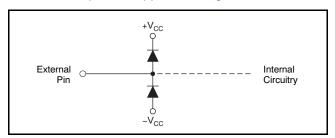


Figure 25. Internal ESD Protection

These diodes provide moderate protection to input overdrive voltages above the supplies as well. The protection diodes can typically support 30-mA continuous current. Where higher currents are possible (for example, in systems with ±12-V supply parts driving into the OPA653), current limiting series resistors should be added into the two inputs. Keep these resistor values as low as possible because high values degrade both noise performance and frequency response.

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EVALUATION MODULE

Schematic and PCB Layout

Figure 26 is the OPA653EVM schematic. Layers 1 through 4 of the PCB are shown in Figure 27. It is recommended to follow the layout of the external components near to the amplifier, ground plane construction, and power routing as closely as possible.

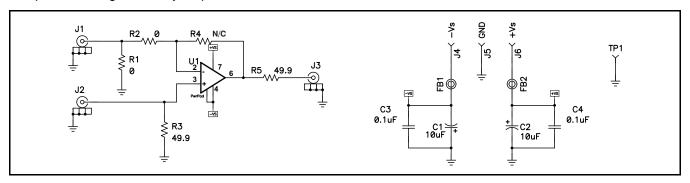


Figure 26. OPA653EVM Schematic

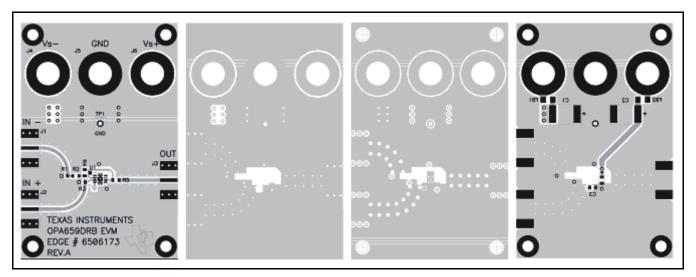


Figure 27. OPA653EVM PCB Layers 1 through 4



Bill of Materials

Table 1 lists the bill of materials for the OPA653EVM as supplied from TI.

Table 1. OPA653EVM Parts List

ITEM	DESCRIPTION	SMD SIZE	REFERENCE DESIGNATOR	QUANTITY	MANUFACTURER PART NUMBER
1	Cap, 10.0 μF, Tantalum, 10%, 35 V	D	C1, C2	2	(AVX) TAJ106K035R
2	Cap, 0.1 μF, Ceramic, X7R, 16 V	0603	C3, C4	2	(AVX) 0603YC104KAT2A
3	Resistor, 0 Ω	0603	R1, R2	2	(ROHM) MCR03EZPJ000
4	Open	0603	R4	1	
5	Resistor, 49.9 Ω, 1/10W, 1%	0603	R3, R5	2	(ROHM) MCR03EZPFX49R9
6	Jack, Banana Receptance, 0.25-in dia. hole		J4, J5, J8	3	(SPC) 813
7	Connector, Edge, SMA PCB jack		J1, J2, J3	3	(JOHNSON) 142-0701-801
8	Test Point, Black		TP1	1	(KEYSTONE) 5001
9	IC, OPA653		U1	1	(TI) OPA653DRB
10	Standoff, 4-40 Hex, 0.625-in length			4	(KEYSTONE) 1808
11	Screw, Phillips, 4-40, .250 in			4	SHR-0440-016-SN
12	Board, Printed Circuit			1	(TI) EDGE# 6506174
13	Bead, Ferrite, 3 A, 80 Ω	1206	FB1, FB2	2	(STEWARD) HI1206N800R-00



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EVM WARNINGS AND RESTRICTIONS

It is important to operate this EVM within the input voltage range of ±3.5 V to ±6.5 V split-supply and the output voltage range of ±3.5 V to ±6.5 V power-supply voltage; do not exceed ±6.5 V power-supply voltage.

Exceeding the specified input range may cause unexpected operation and/or irreversible damage to the EVM. If there are questions concerning the input range, please contact a TI field representative prior to connecting the input power.

Applying loads outside of the specified output range may result in unintended operation and/or possible permanent damage to the EVM. Please consult the EVM User's Guide prior to connecting any load to the EVM output. If there is uncertainty as to the load specification, please contact a TI field representative.

During normal operation, some circuit components may have case temperatures greater than +85°C. The EVM is designed to operate properly with certain components above +85°C as long as the input and output ranges are maintained. These components include but are not limited to linear regulators, switching transistors, pass transistors, and current sense resistors. These types of devices can be identified using the EVM schematic located in the EVM User's Guide. When placing measurement probes near these devices during operation, please be aware that these devices may be very warm to the touch.

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22-Dec-2008

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
OPA653IDBVR	PREVIEW	SOT-23	DBV	5	3000	TBD	Call TI	Call TI
OPA653IDBVT	PREVIEW	SOT-23	DBV	5	250	TBD	Call TI	Call TI
OPA653IDRBR	ACTIVE	SON	DRB	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
OPA653IDRBT	ACTIVE	SON	DRB	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



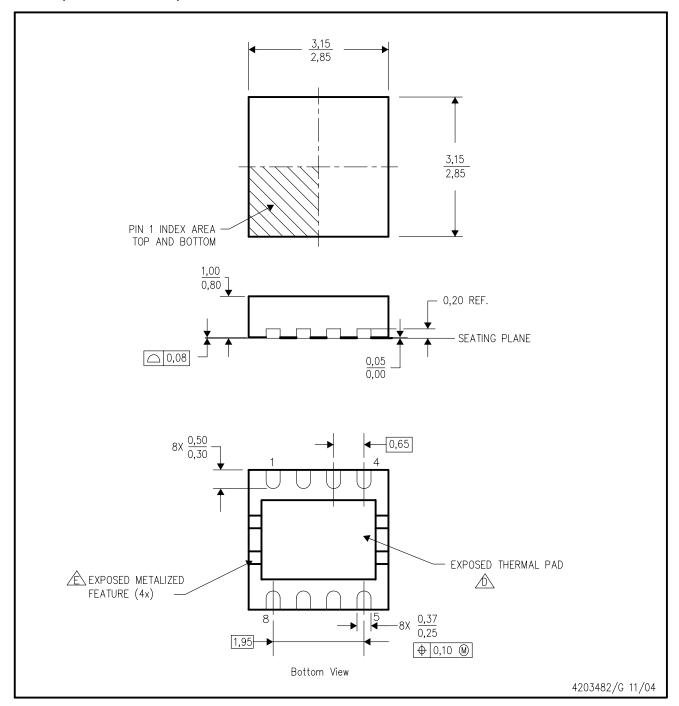
NOTES:

- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Falls within JEDEC MO-178 Variation AA.



DRB (S-PDSO-N8)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- C. Small Outline No-Lead (SON) package configuration.
- The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions.
- Metalized features are supplier options and may not be on the package.



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